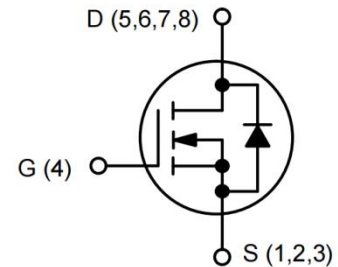


1、Description

SS007N04NS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

Schematic Diagram



KEY CHARACTERISTICS

Parameter	Value	Unit
V _{DSS}	40	V
I _D	290	A
R _{DS(on).typ}	0.65	mΩ

FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 0.8m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Synchronous rectification
- Power tool
- Motor drivers
- Battery formation

ORDERING INFORMATION:

Ordering Codes	Package	Product Code	Packing	Quantity
SS007N04NS	PDFN5X6	SS007N04NS	Reel	5000

